

Amendments to the Claims:

Please note that all claims currently pending and under consideration in the referenced application are shown below. This listing of claims will replace all prior versions and listings of claims in the application. Please cancel claims 1, 2, 6 and 7, without prejudice to the filing of one or more applications including same.

Listing of Claims:

Claims 1-2 (Canceled)

3. (Original) A semiconductor device for operable connection to a carrier substrate, the semiconductor device comprising:

a regulator circuit for receiving an electrical power signal;

a semiconductor substrate;

active circuit devices on the semiconductor substrate; and

an on-chip capacitor having at least a portion thereof formed in an active area of the

semiconductor substrate, the on-chip capacitor being operably coupled to the regulator circuit and operably coupled to the active circuit devices to provide filtering capacitance for the semiconductor device.

4. (Original) The semiconductor device of claim 3, wherein the on-chip capacitor comprises a planar-type capacitor.

5. (Previously presented) The semiconductor device of claim 3, wherein the on-chip capacitor includes a first node and a second node, one node of the first and second nodes comprising a poly layer and the other node of the first and second nodes comprising a channel.

Claims 6-7 (Canceled)

8. (Original) A semiconductor device for connection to a carrier substrate configured to provide power and ground thereto, the semiconductor device comprising:
a semiconductor substrate having active circuit elements formed on an active area thereof;
at least one regulator circuit for receiving power; and
at least one capacitor on the semiconductor substrate, at least a portion of the at least one capacitor being formed on the active area, the at least one capacitor being operably coupled to the at least one regulator circuit and to the active circuit elements to provide filtering capacitance for the active circuit elements when the semiconductor device is operably connected to power and ground of the carrier substrate

9. (Original) The semiconductor device of claim 8, wherein the at least one capacitor comprises a planar-type capacitor.

10. (Previously presented) The semiconductor device of claim 8, wherein the at least one capacitor includes a first node and a second node, one node of the first and second nodes comprising a poly layer and the other node of the first and second nodes comprising a channel.